

| | |
|---------------------|---------------|
| V_{DSS} | 1700V |
| $R_{DS(on)}$ (Typ.) | 1.15 Ω |
| I_D | 4A |
| P_D | 44W |

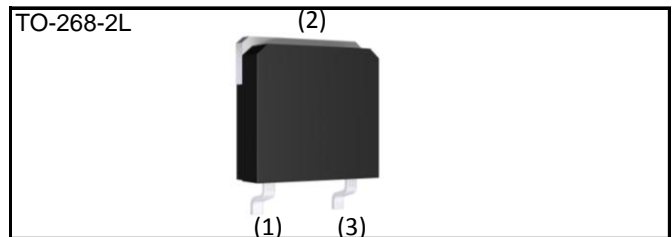
●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating ; RoHS compliant

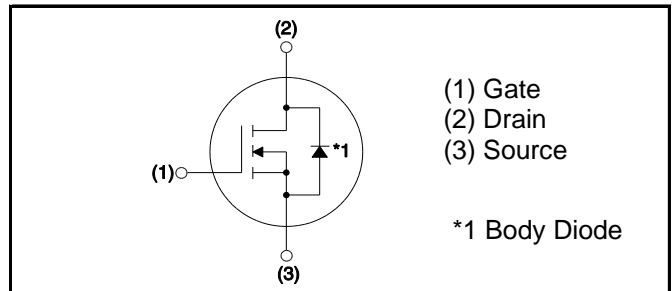
●Application

- Auxiliary power supplies
- Switch mode power supplies

●Outline



●Inner circuit



●Packaging specifications

| Type | Packing | Embossed tape |
|------|---------------------------|---------------|
| | Reel size (mm) | 330 |
| | Tape width (mm) | 24 |
| | Basic ordering unit (pcs) | 400 |
| | Taping code | TB |
| | Marking | SCT2H12NY |

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit | |
|--|---------------------------|-------------|------------------|---|
| Drain - Source voltage | V_{DSS} | 1700 | V | |
| Continuous drain current | $T_c = 25^\circ\text{C}$ | I_D^{*1} | 4 | A |
| | $T_c = 100^\circ\text{C}$ | I_D^{*1} | 2.9 | A |
| Pulsed drain current | $I_{D,pulse}^{*2}$ | 10 | A | |
| Gate - Source voltage (DC) | V_{GSS} | -6 to 22 | V | |
| Gate - Source surge voltage ($t_{surge} < 300\text{nsec}$) | $V_{GSS,surge}^{*3}$ | -10 to 26 | V | |
| Power dissipation ($T_c = 25^\circ\text{C}$) | P_D | 44 | W | |
| Junction temperature | T_j | 175 | $^\circ\text{C}$ | |
| Range of storage temperature | T_{stg} | -55 to +175 | $^\circ\text{C}$ | |

● Thermal resistance

| Parameter | Symbol | Values | | | Unit |
|-------------------------------------|------------|--------|------|------|------|
| | | Min. | Typ. | Max. | |
| Thermal resistance, junction - case | R_{thJC} | - | 2.65 | 3.45 | °C/W |

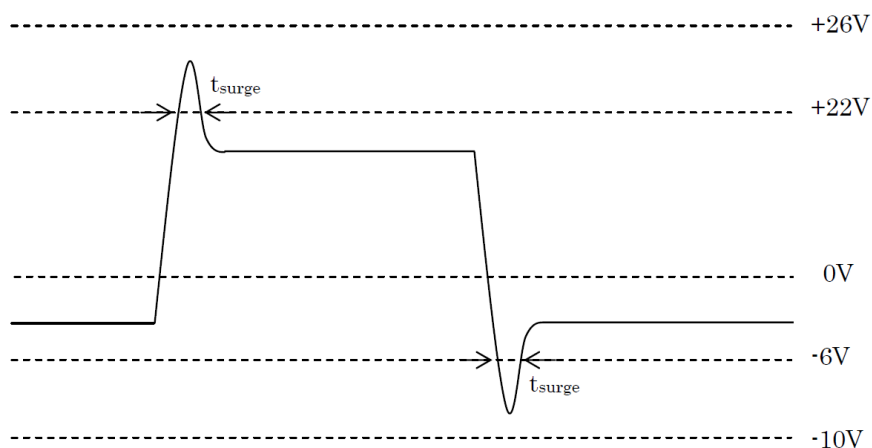
● Electrical characteristics ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Conditions | Values | | | Unit |
|----------------------------------|---------------|---|--------|------|------|---------------|
| | | | Min. | Typ. | Max. | |
| Drain - Source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{V}, I_D = 1\text{mA}$ | 1700 | - | - | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 1700\text{V}, V_{GS} = 0\text{V}$ $T_j = 25^\circ\text{C}$ | - | 0.1 | 10 | μA |
| | | $T_j = 150^\circ\text{C}$ | - | 0.2 | - | |
| Gate - Source leakage current | I_{GSS+} | $V_{GS} = +22\text{V}, V_{DS} = 0\text{V}$ | - | - | 100 | nA |
| Gate - Source leakage current | I_{GSS-} | $V_{GS} = -6\text{V}, V_{DS} = 0\text{V}$ | - | - | -100 | nA |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 0.41\text{mA}$ | 1.6 | 2.8 | 4.0 | V |

*1 Limited only by maximum temperature allowed.

*2 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Example of acceptable V_{GS} waveform



*4 Pulsed

●Electrical characteristics (T_a = 25°C)

| Parameter | Symbol | Conditions | Values | | | Unit |
|--|-----------------------------------|---|--------|--------------|----------|------|
| | | | Min. | Typ. | Max. | |
| Static drain - source on - state resistance | R _{DS(on)} ^{*4} | V _{GS} = 18V, I _D = 1.1A T _j = 25°C T _j = 125°C | - - | 1.15 1.71 | 1.5 - | Ω |
| Gate input resistance | R _G | f = 1MHz, open drain | - | 64 | - | Ω |
| Transconductance | g _{fs} ^{*4} | V _{DS} = 10V, I _D = 1.1A | - | 0.4 | - | S |
| Input capacitance | C _{iss} | V _{GS} = 0V | - | 184 | - | pF |
| Output capacitance | C _{oss} | V _{DS} = 800V | - | 16 | - | |
| Reverse transfer capacitance | C _{rss} | f = 1MHz | - | 6 | - | |
| Effective output capacitance, energy related | C _{o(er)} | V _{GS} = 0V V _{DS} = 0V to 800V | - | 17 | - | pF |
| Turn - on delay time | t _{d(on)} ^{*4} | V _{DD} = 500V, I _D = 1.1A | - | 16 | - | ns |
| Rise time | t _r ^{*4} | V _{GS} = 18V/0V | - | 21 | - | |
| Turn - off delay time | t _{d(off)} ^{*4} | R _L = 455Ω | - | 35 | - | |
| Fall time | t _f ^{*4} | R _G = 0Ω | - | 74 | - | |
| Turn - on switching loss | E _{on} ^{*4} | V _{DD} = 800V, I _D = 1.1A V _{GS} = 18V/0V R _G = 0Ω, L = 2mH | - | 57 | - | μJ |
| Turn - off switching loss | E _{off} ^{*4} | *E _{on} includes diode reverse recovery | - | 32 | - | |

●Gate Charge characteristics (T_a = 25°C)

| Parameter | Symbol | Conditions | Values | | | Unit |
|----------------------|-------------------------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Total gate charge | Q _g ^{*4} | V _{DD} = 500V | - | 14 | - | nC |
| Gate - Source charge | Q _{gs} ^{*4} | I _D = 1A | - | 4 | - | |
| Gate - Drain charge | Q _{gd} ^{*4} | V _{GS} = 18V | - | 5 | - | |
| Gate plateau voltage | V _(plateau) | V _{DD} = 500V, I _D = 1A | - | 10.5 | - | V |

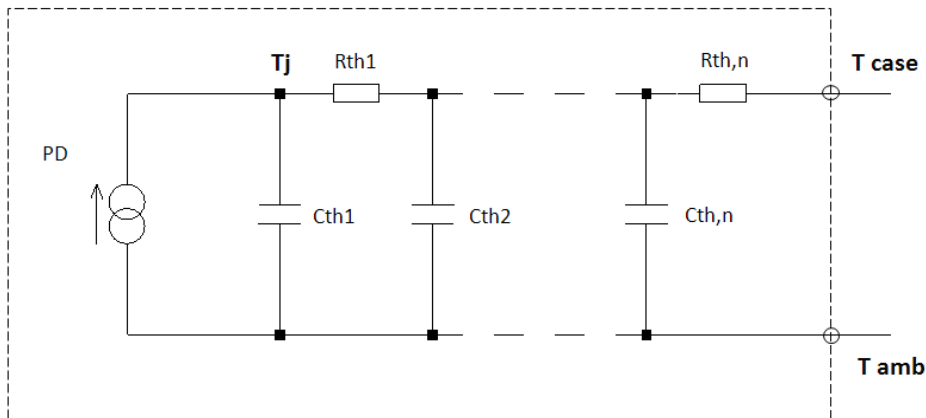
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|----------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Inverse diode continuous, forward current | I_S^{*1} | $T_c = 25^\circ\text{C}$ | - | - | 4 | A |
| Inverse diode direct current, pulsed | I_{SM}^{*2} | | - | - | 10 | A |
| Forward voltage | V_{SD}^{*4} | $V_{GS} = 0\text{V}, I_S = 1.1\text{A}$ | - | 4.3 | - | V |
| Reverse recovery time | t_{rr}^{*4} | $I_F = 1.1\text{A}, V_R = 800\text{V}$ $di/dt = 300\text{A}/\mu\text{s}$ | - | 21 | - | ns |
| Reverse recovery charge | Q_{rr}^{*4} | | - | 13 | - | nC |
| Peak reverse recovery current | I_{rrm}^{*4} | | - | 1.1 | - | A |

●Typical Transient Thermal Characteristics

| Symbol | Value | Unit |
|-----------|-------|------|
| R_{th1} | 493m | K/W |
| R_{th2} | 1601m | |
| R_{th3} | 556m | |

| Symbol | Value | Unit |
|-----------|-----------|------|
| C_{th1} | 378 μ | Ws/K |
| C_{th2} | 1.42m | |
| C_{th3} | 65.6m | |



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

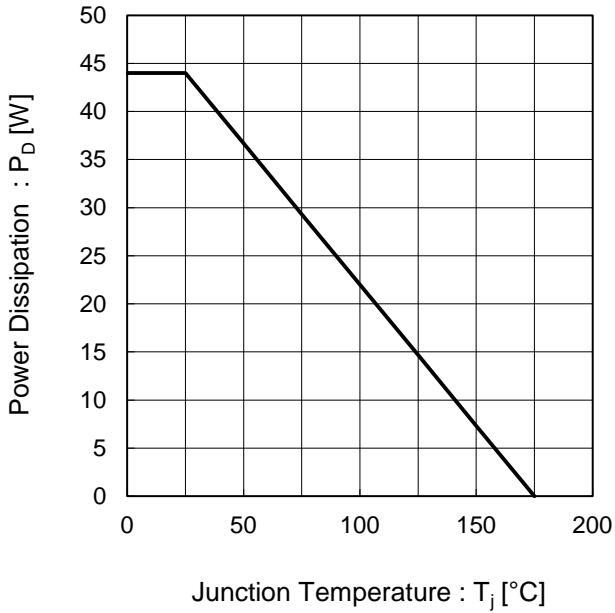


Fig.2 Maximum Safe Operating Area

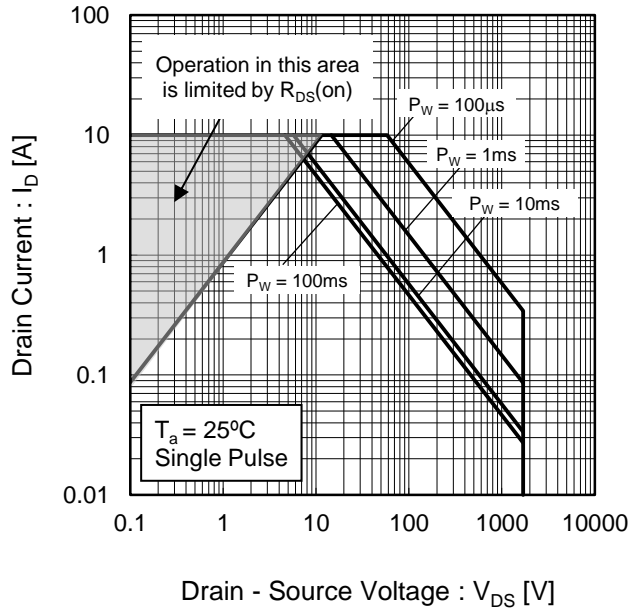
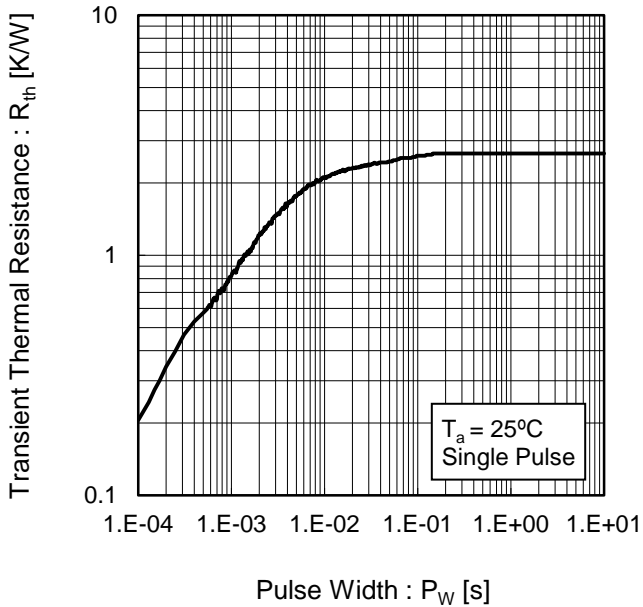


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

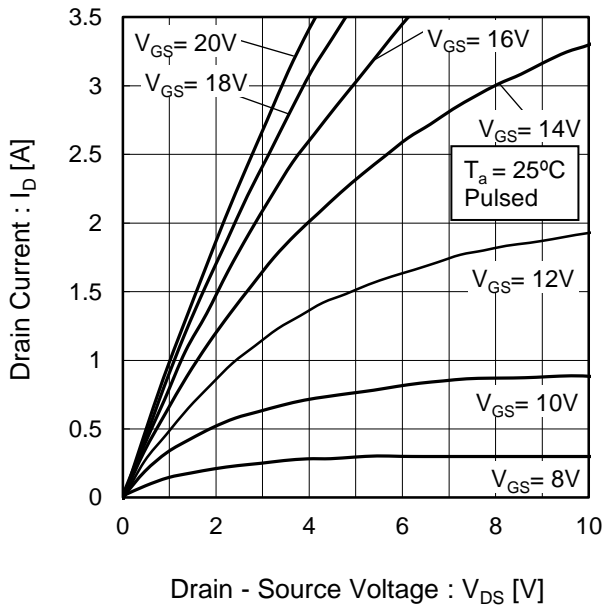


Fig.5 Typical Output Characteristics(II)

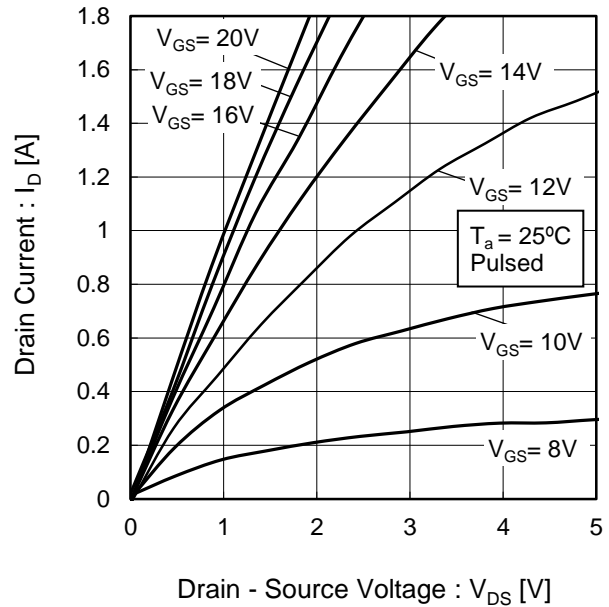


Fig.6 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

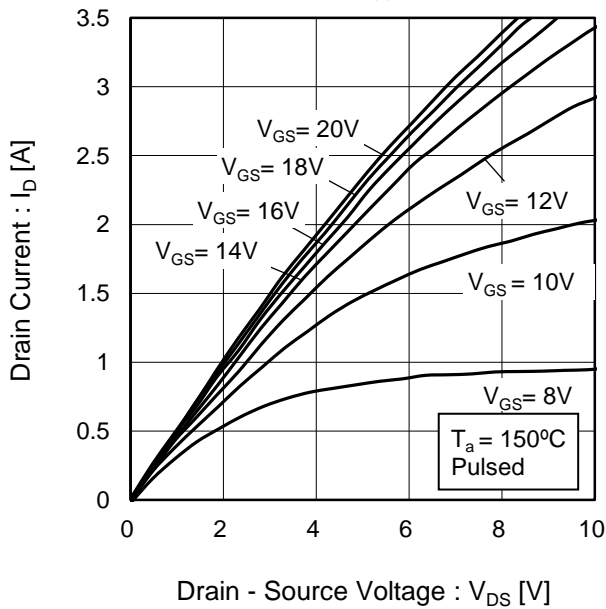
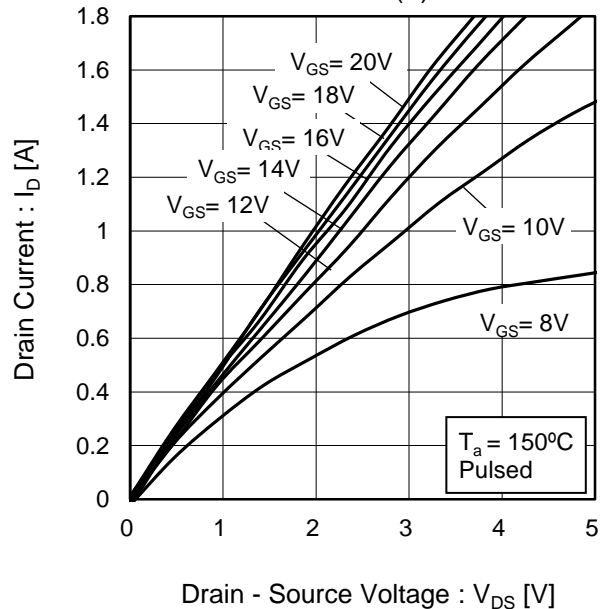


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

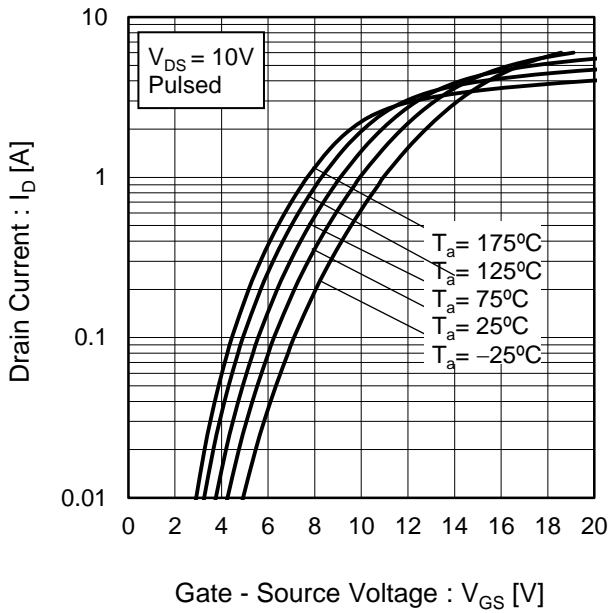


Fig.9 Typical Transfer Characteristics (II)

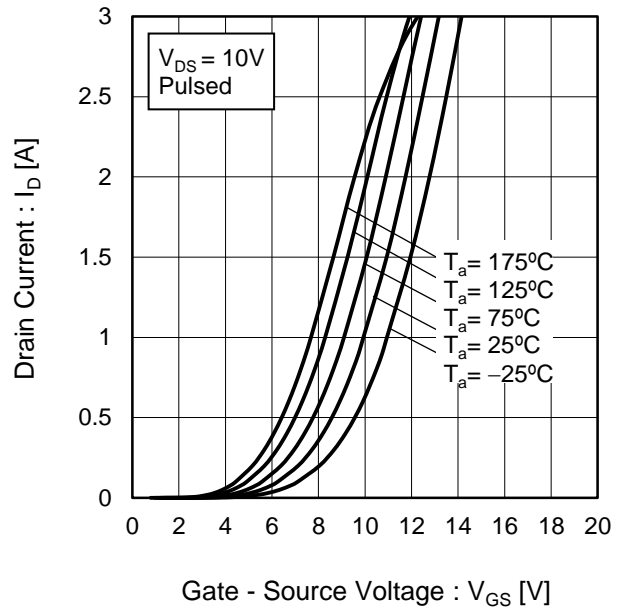


Fig.10 Gate Threshold Voltage vs. Junction Temperature

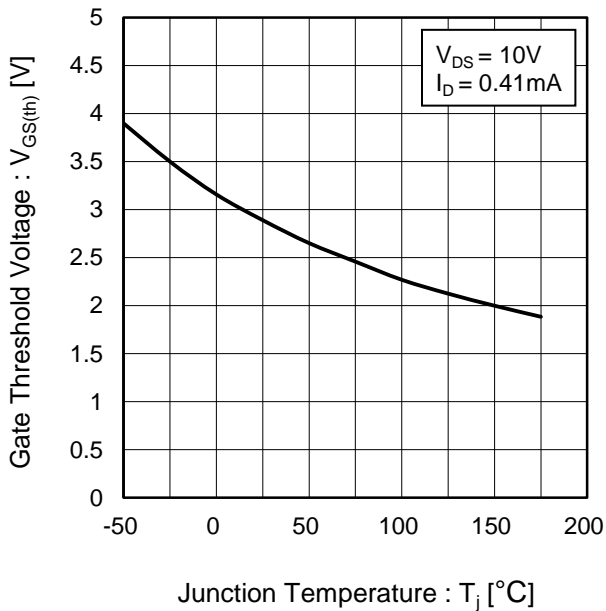
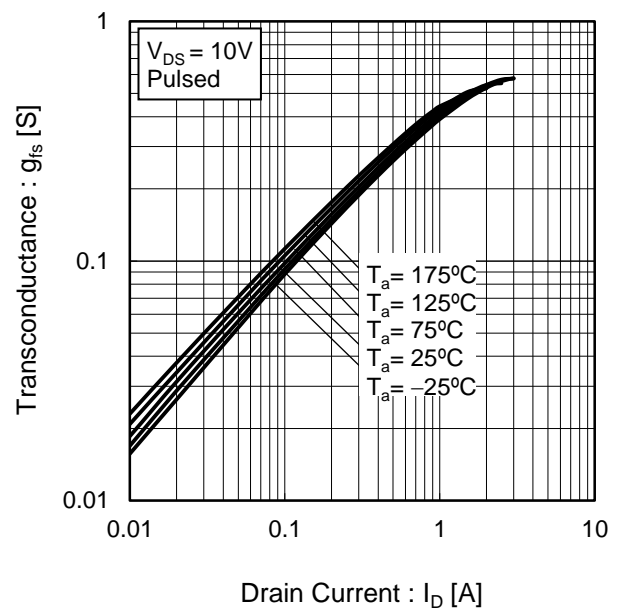


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

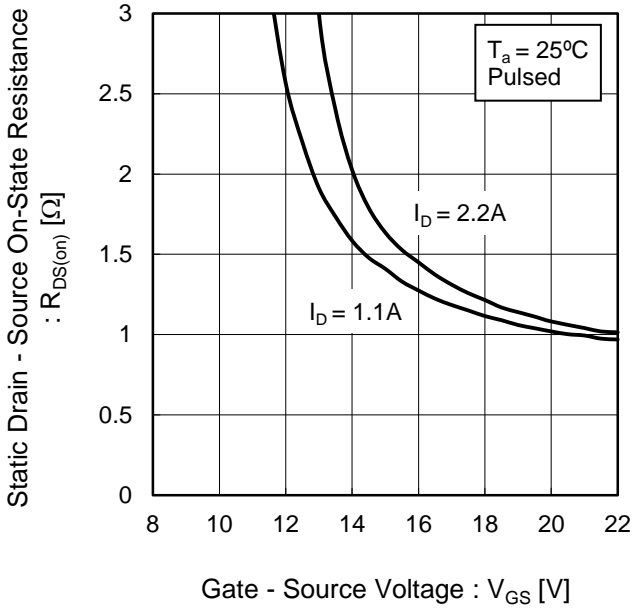


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

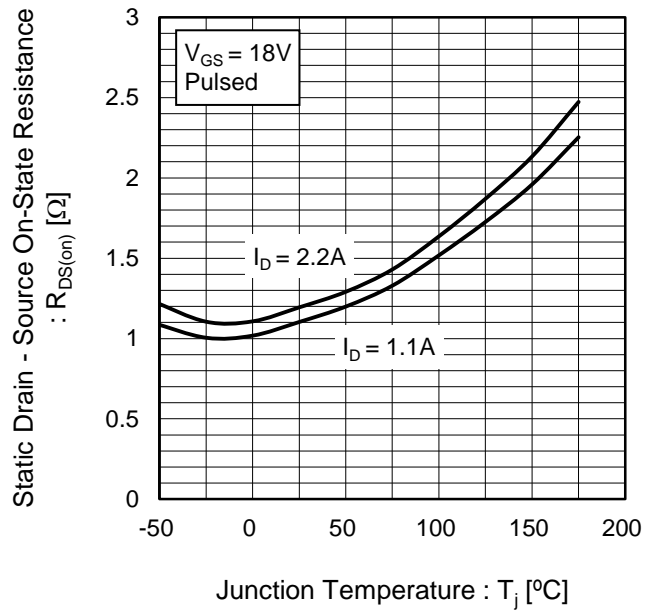
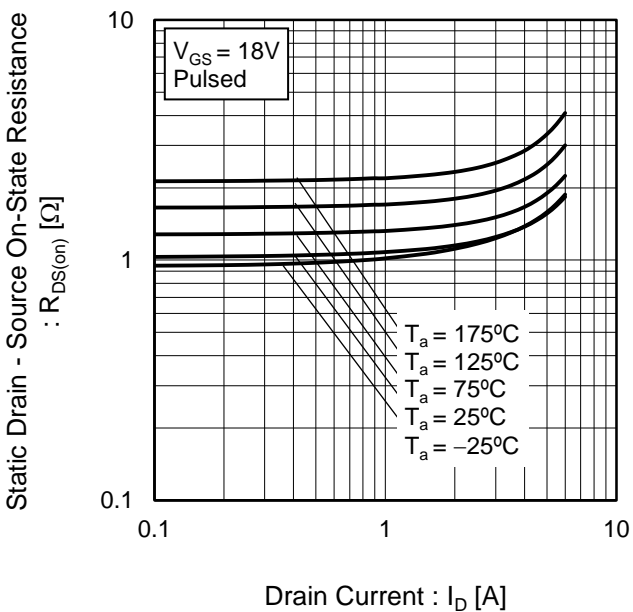


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

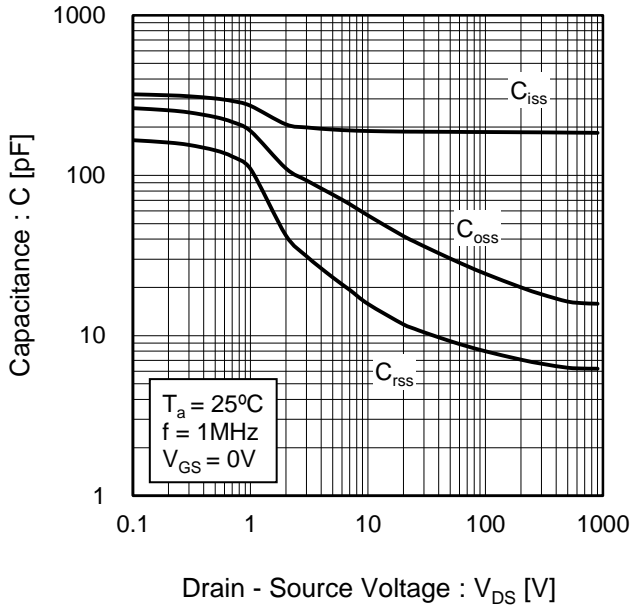


Fig.16 Coss Stored Energy

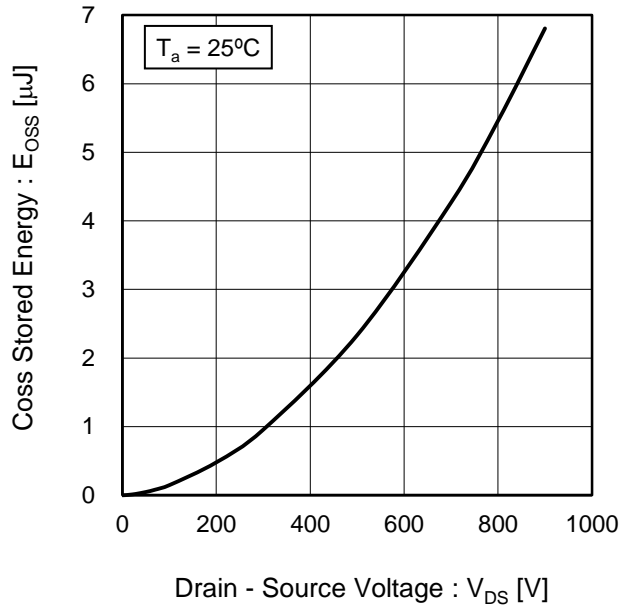


Fig.17 Switching Characteristics

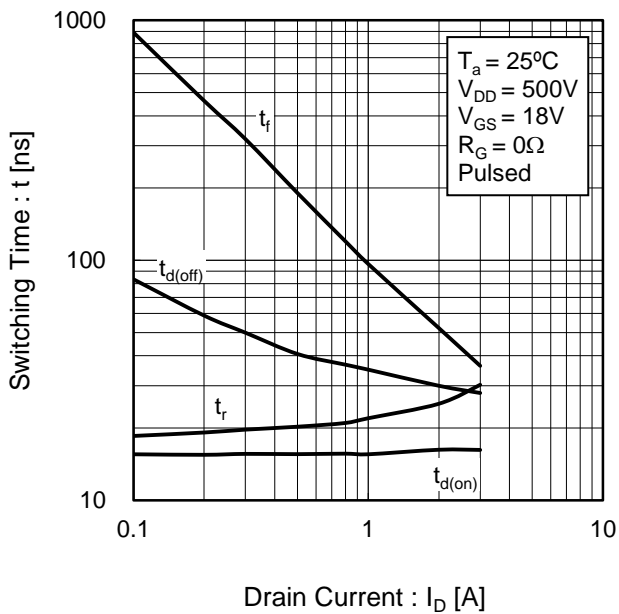
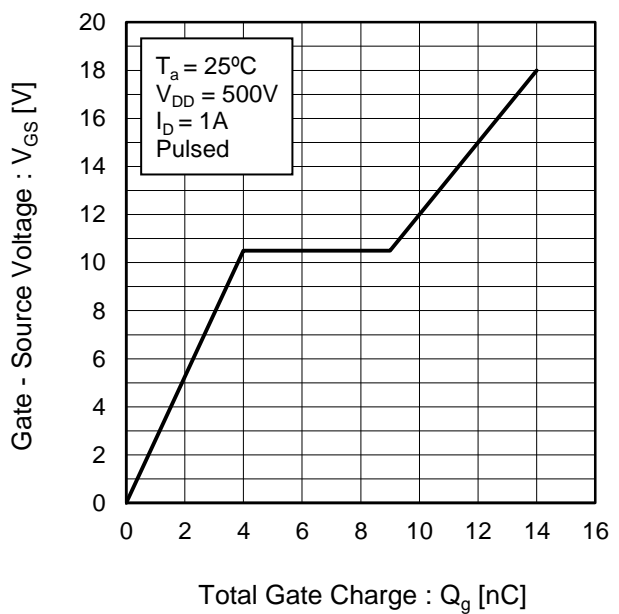


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

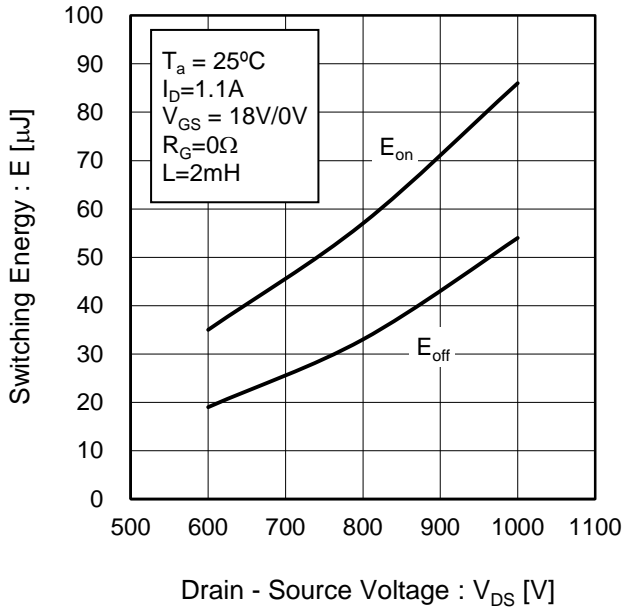


Fig.20 Typical Switching Loss vs. Drain Current

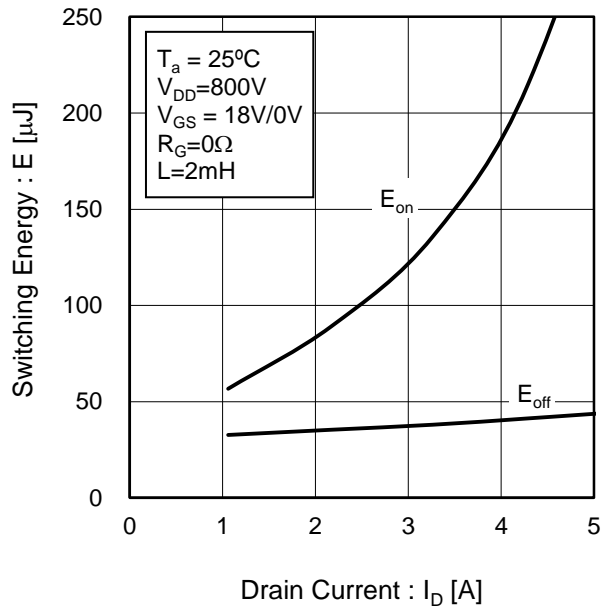
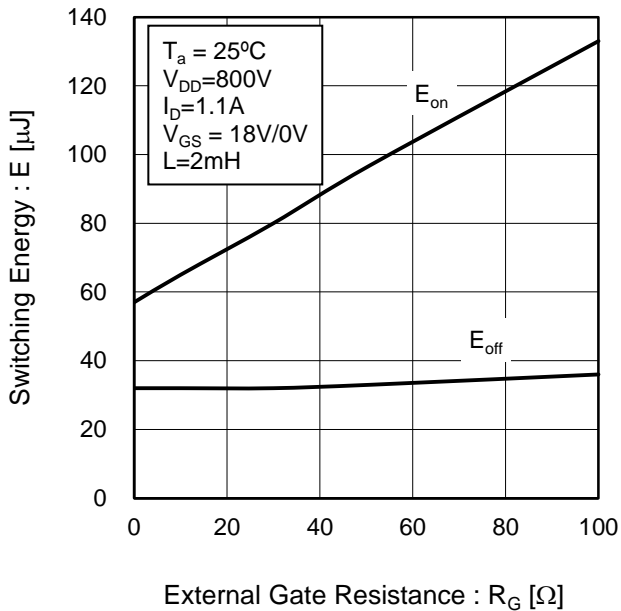


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

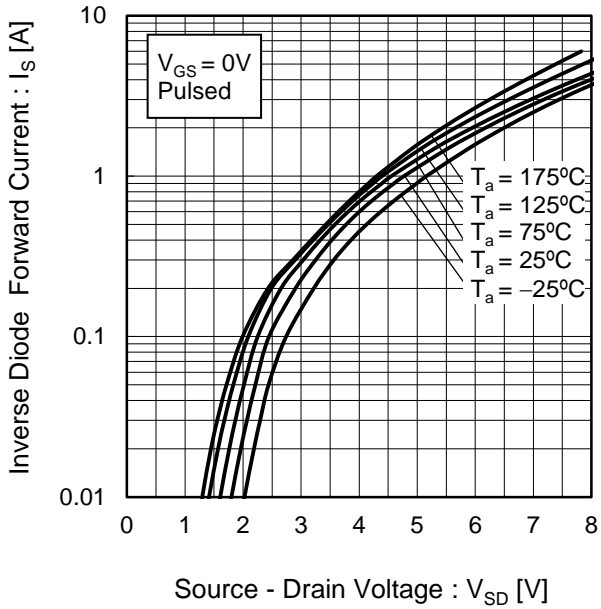
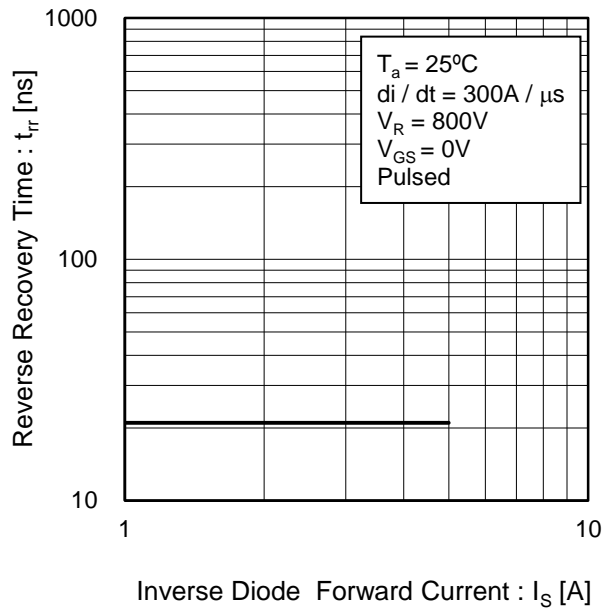


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

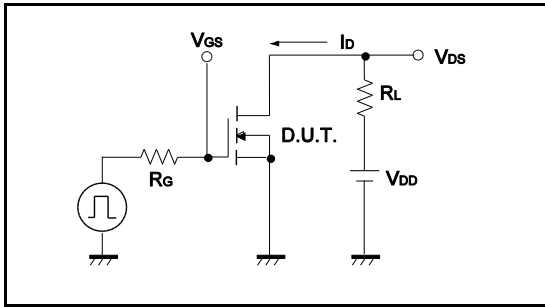


Fig.1-2 Switching Waveforms

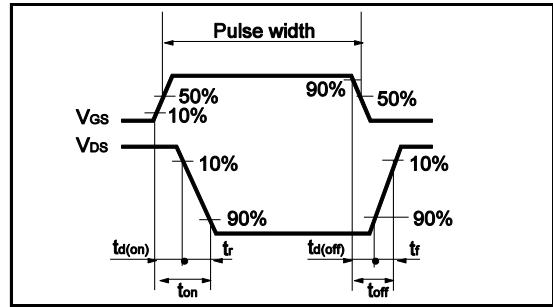


Fig.2-1 Gate Charge Measurement Circuit

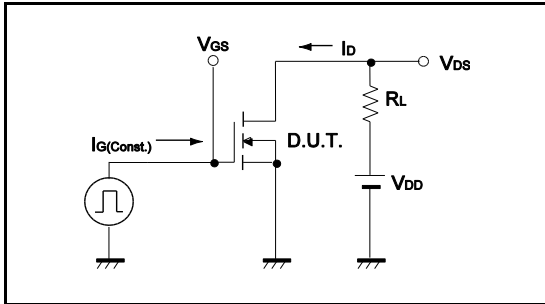


Fig.2-2 Gate Charge Waveform

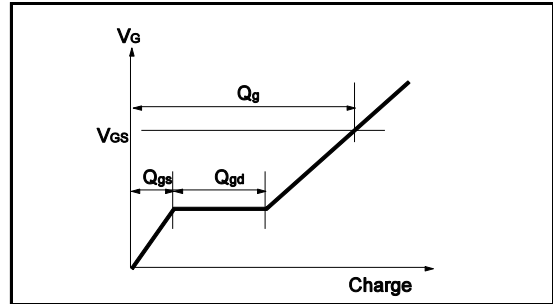


Fig.3-1 Switching Energy Measurement Circuit

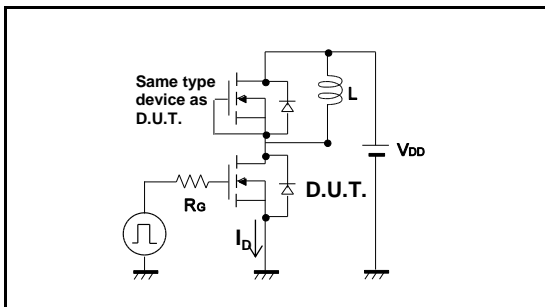


Fig.3-2 Switching Waveforms

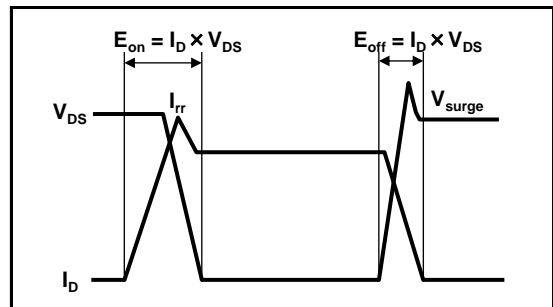


Fig.4-1 Reverse Recovery Time Measurement Circuit

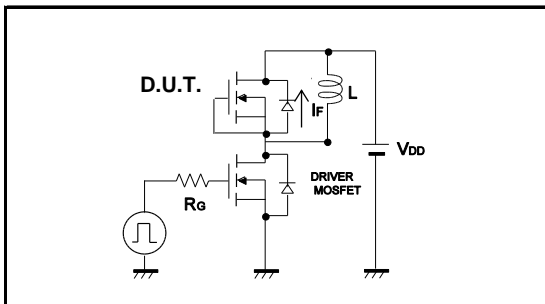
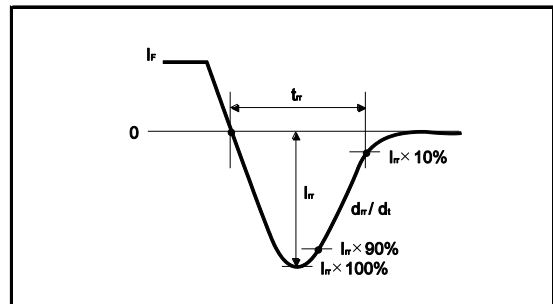
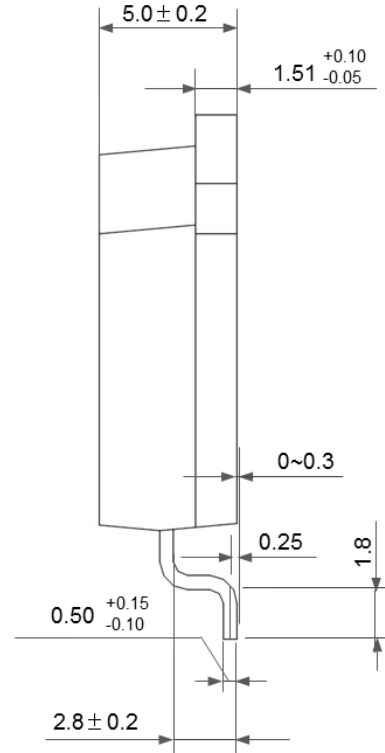
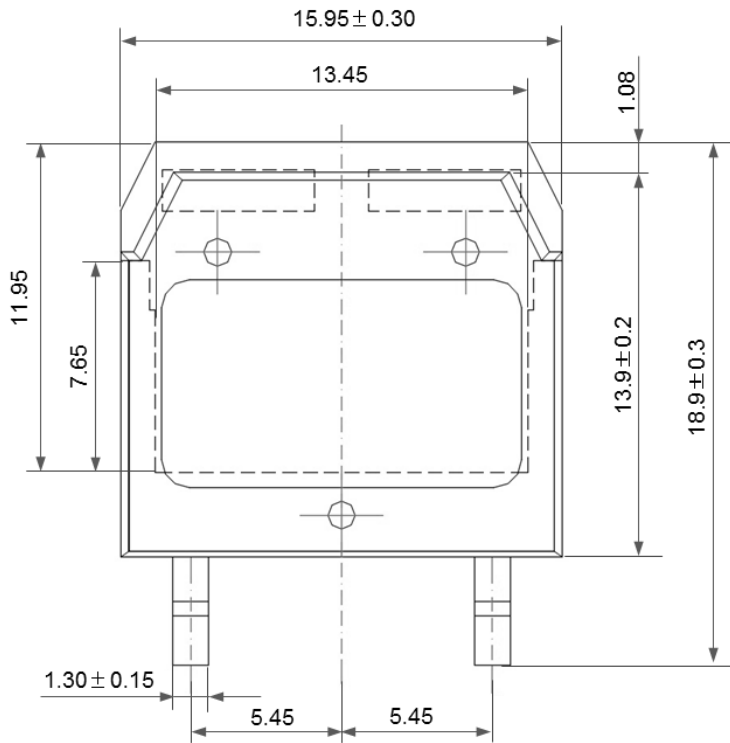


Fig.4-2 Reverse Recovery Waveform



●Dimensions (Unit : mm)

TO-268-2L



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| Part Number | SCT2H12NY |
| Package | TO-268-2L |
| Unit Quantity | 800 |
| Minimum Package Quantity | 800 |
| Packing Type | Taping |
| Constitution Materials List | inquiry |
| RoHS | Yes |